

General Description

The WSF50N10G is the highest performance SGT N-Ch MOSFET to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

Features

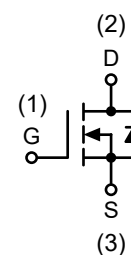
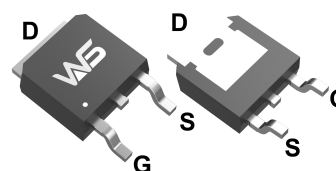
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

100V	13.8mΩ	40A

Applications

- Consumer electronic power supply
- Motor control
- Synchronous-rectification
- Isolated DC

TO-252-2 Pin Configuration



Absolute Maximum Ratings (TC=25 °C,

Symbol	Parameter	Rating	Units
VDS	Drain source voltage	100	V
VGS	Gate source voltage	±20	V
ID	Continuous drain current ¹⁾	TC=25 °C 40	A
ID, pulse	Pulsed drain current ²⁾	TC=25 °C 120	A
P _D	Power dissipation ³⁾	TC=25 °C 71	W
EAS	Single pulsed avalanche energy ⁵⁾	57	mJ
T _{stg} , T _j	Operation and storage temperature	-55 to 150	°C
R _{θJC}	Thermal resistance, junction-case	1.76	°C/W
R _{θJA}	Thermal resistance, junction-ambient ⁴⁾	62	°C/W

$^{\circ}\text{C}$,

BVDSS	Drain-source breakdown voltage	$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$	100	107	-	V
VGS(th)	Gate threshold voltage	$V_{DS}=V_{GS}$, $I_D=250\ \mu\text{A}$	1.2	1.5	2.5	V
RDS(ON)	Drain-source on-state resistance	$V_{GS}=10\text{ V}$, $I_D=10\text{ A}$	-	13.8	20.0	m Ω
RDS(ON)	Drain-source on-state resistance	$V_{GS}=4.5\text{ V}$, $I_D=7\text{ A}$	-	17.4	26.0	m Ω
IGSS	Gate-source leakage current	$V_{GS}=\pm 20\text{ V}$	-	-	± 100	nA
IDSS	Drain-source leakage current	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$	-	-	1	μA
Ciss	Input capacitance	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$	-	1003.9	-	pF
Coss	Output capacitance		-	185.4	-	pF
Crss	Reverse transfer capacitance		-	9.8	-	pF
td(on)	Turn-on delay time	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $R_G=10\ \Omega$, $I_D=5\text{ A}$	-	16.6	-	ns
tr	Rise time		-	3.8	-	ns
td(off)	Turn-off delay time		-	75.5	-	ns
tf	Fall time		-	46	-	ns
Qg	Total gate charge	$I_D=5\text{ A}$, $V_{DS}=50\text{ V}$, $V_{GS}=10\text{ V}$	-	16.2	-	nc
Qgs	Gate-source charge		-	2.8	-	nc
Qgd	Gate-drain charge		-	4.1	-	nc
Vplateau	Gate plateau voltage		-	3	-	V
Is	Diode forward current	$V_{GS}<V_{th}$	-	30	-	A
ISP	Pulsed source current		-	90	-	A
trr	Reverse recovery time	$I_S=1\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$	49	-	-	ns
Qrr	Reverse recovery charge		61.8	-	-	nc
Irrm	Peak reverse recovery current		2.4	-	-	A

Note

- 1、 Calculated continuous current based on maximum allowable junction temperature.
- 2、 Repetitive rating; pulse width limited by max. junction temperature.
- 3、 Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4、 The value of $R_{\theta ja}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\ ^{\circ}\text{C}$.
- 5、 $V_{DD}=50\text{ V}$, $R_G=25\ \Omega$, $L=0.3\text{ mH}$, starting $T_j=25\ ^{\circ}\text{C}$.

Qvmf @e o bofp f p

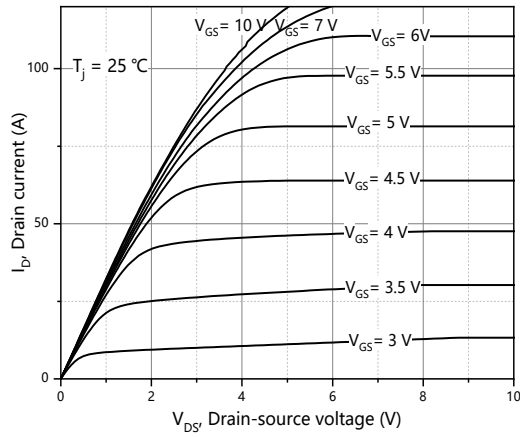


Figure 1, Typ. output characteristics

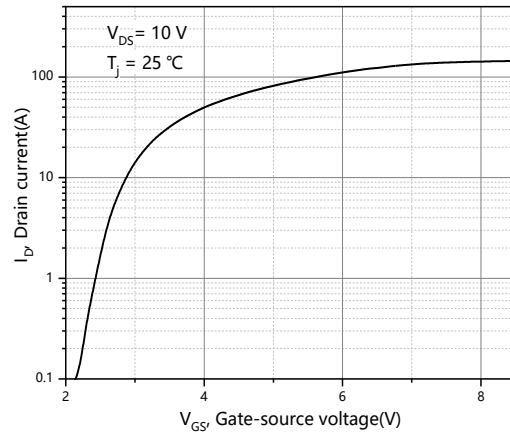


Figure 2, Typ. transfer characteristics

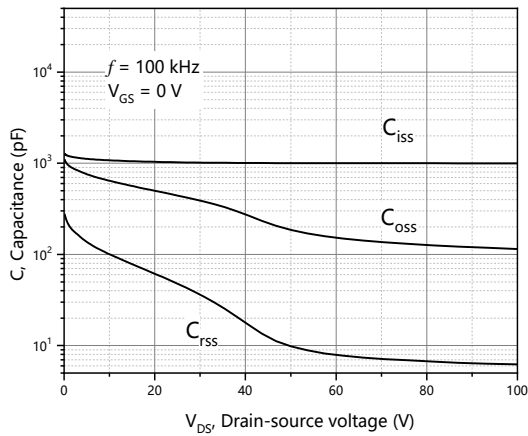


Figure 3, Typ. capacitances

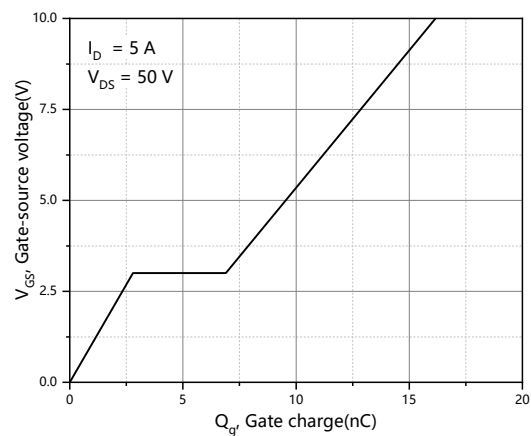


Figure 4, Typ. gate charge

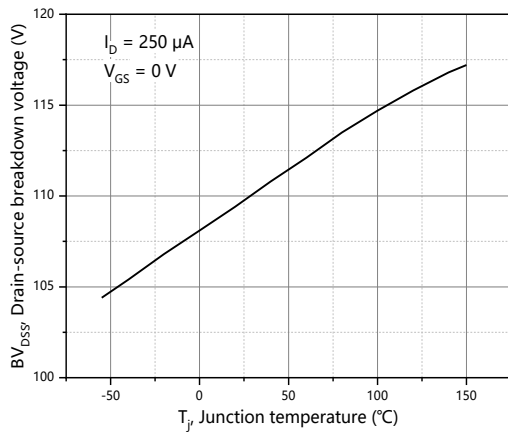


Figure 5, Drain-source breakdown voltage

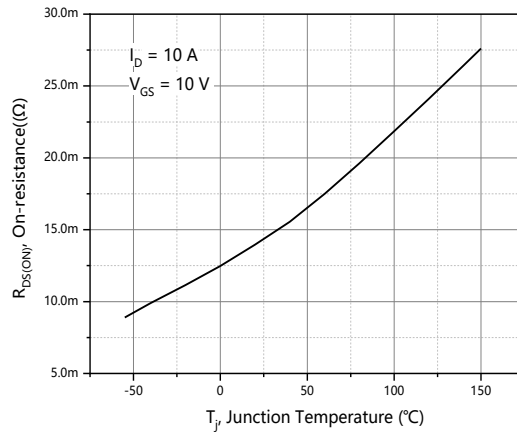


Figure 6, Drain-source on-state resistance

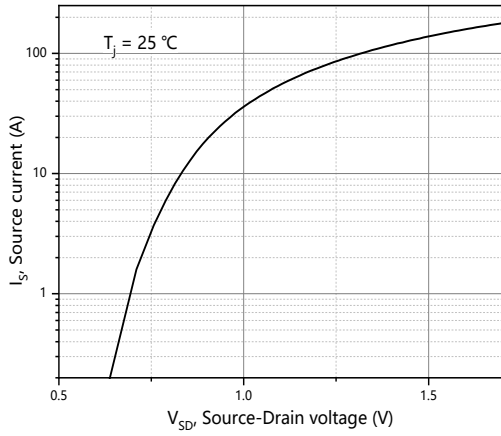


Figure 7, Forward characteristic of body diode

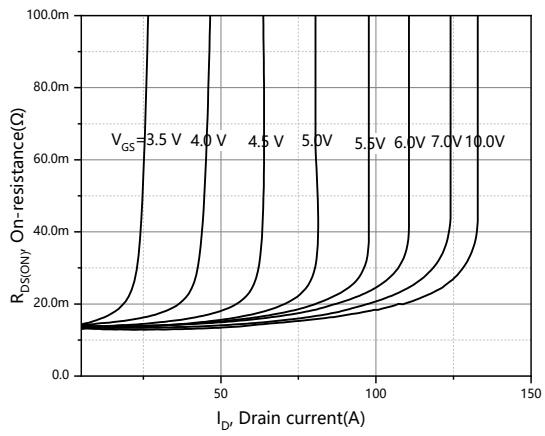


Figure 8, Drain-source on-state resistance

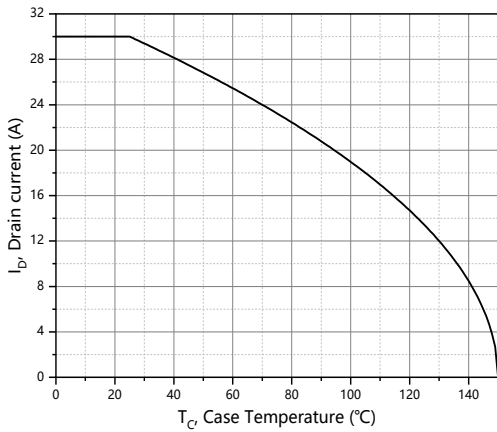


Figure 9, Drain current

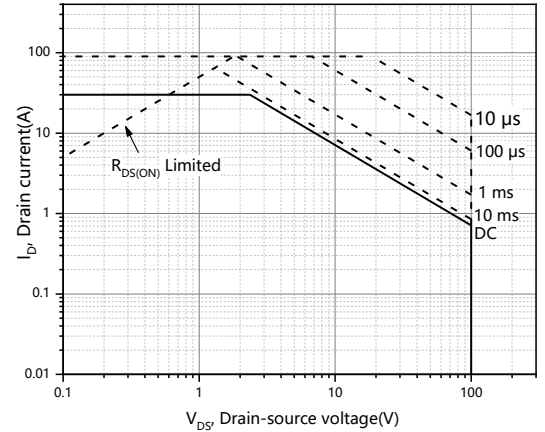
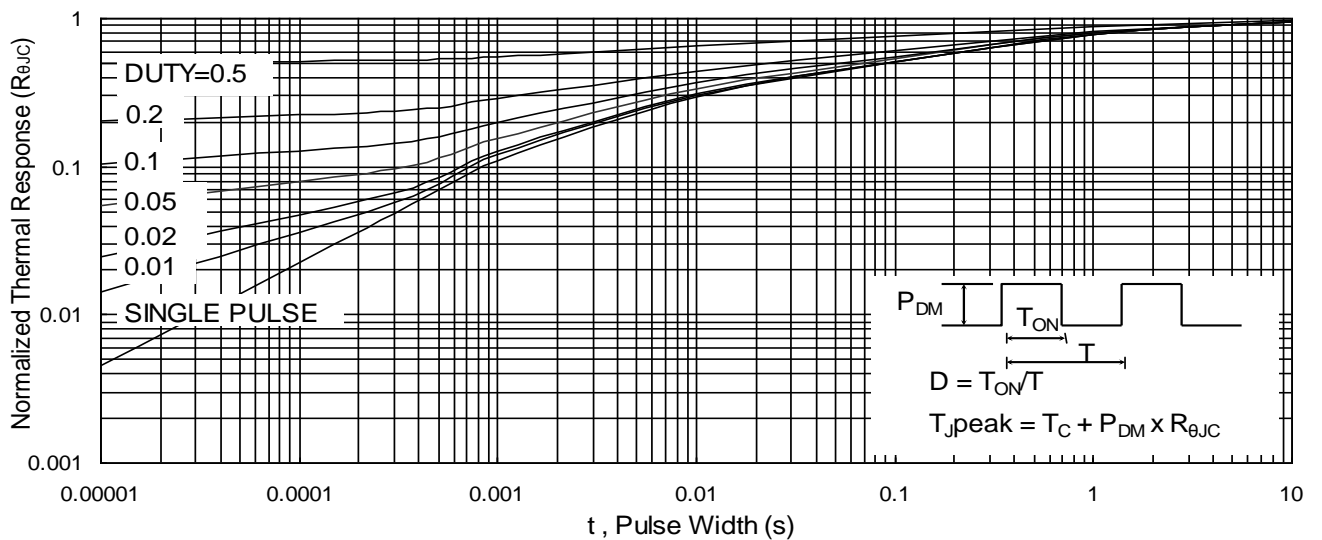


Figure 10, Safe operation area $T_C=25\text{ }^\circ\text{C}$



)LJXR UPDOLHG0DLPR7UDQVLHQW7KHUPDO,PSHGDQFH



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